**Introduction:**

Solid-state drives (SSDs) are widely used in today’s computer systems. Due to their high read and write throughput, low response time, resilient to physical shock, a small form factor, consuming less static power, and decreasing cost (cost-per-bit), SSDs have replaced traditional magnetic hard disk drives (HDDs) in many datacenters and enterprise servers, as well as in consumer devices.

Modern solid-state drives can be abstracted into three levels: (1) NAND Flash physics, (2) integrated circuit architecture, and (3) SSD firmware, as shown in . At the lowest level of abstraction is the NAND Flash physics, which describes the motion of electrons for the basic operations (i.e., program, read, and erase) for a single NAND Flash memory cell. Above the NAND Flash physics level is the integrated circuit architecture level. This level … . Then, the top level is SSD firmware, which … .

SSD Firmware

Integrated Circuit Architecture

NAND Flash Physics

Software

Hardware

Electrons

We will first dive into the lowest level, NAND Flash physics, to understand the characteristics of NAND Flash since its unique properties decide the upper levels’ structures.

Note the NAND Flash’s unique properties are including:

* Large operation units
* Erase-before-write property
* Asymmetry in operation units
* Limited endurance
* Various error sources
* Asymmetry in operation latencies

(retention loss, schematic, wear leveling->for endurance, Error Correction Code->for reliability, soft decoding, randomization, read retry)

**NAND Flash Physics:**

A floating-gate transistor constitutes a flash memory cell. It can encode one or more bits of digital data, which is represented by the level of charge stored inside the transistor’s floating gate. The transistor traps charge within its floating gate, which dictates the threshold voltage level at which the transistor turns on.

A floating-gate transistor provides nonvolatile memory storage (i.e., the data stored in NAND flash is correctly retained even when the power is disconnected).

(charge trap transistors for 3D)

(retention loss, wear out effect)

**Program of NAND flash cells:**

During the program operation, the cells share the high programming voltage on the selected wordline but the program operation has to be bit selective. Therefore, a high channel potential is needed to reduce the voltage drop across the tunneling dielectric and prevents the electrons tunneling from the channel to the floating gate as indicated.

Note programming a page cannot change ‘0’ cells to ‘1’ cells. Thus, NAND flash cells have erase-before-write property.

**Erase of NAND flash cells:**

The erase operation resets the information of all the cells belonging to one block simultaneously.

Because the granularity of erase operation is usually larger the program operation (block > page), the in-place write on a page is very inefficient. As a result, SSD does out-of-place write and conducts garbage collection to recover free blocks.

**NAND flash memory errors**

NAND flash memory errors can be induced by a variety of sources, including flash cell wearout, disturb effects (errors introduced during programming, interference from operations performed on adjacent cells), and data retention issues due to charge leakage. (three major sources)

**Disturb effects** alter the memory transistors threshold voltage unintentionally during memory access operations under the influence of specific disturb conditions. Since it is essential for an efficient area consumption to arrange the storage transistors in a contact saving way, the sharing of voltage nodes can not be avoided. During the read and program operations, positive voltages are applied to the gate nodes of the memory transistors, wherein the channel is at a lower potential or even grounded. Therefore this condition is called gate disturb (also wordline disturb) and it is the most common disturb mechanism in NAND Flash memory arrays.

(Program disturb and read disturb)

Read disturbs are the most frequent source of disturbs in NAND architectures. This kind of disturb may occur when reading many times the same cell without any erase operation. All the cells belonging to the same string of the cell to be read must be driven in a ON state, independently of their stored charge. The relatively high bias applied on the control gate and the sequence of pulses applied during successive read operation may trigger the Stress Induced Leakage Current (SILC) effects in some cells that, therefore, may gain charge. Note read disturbs do not provoke permanent oxide damages: if erased and then reprogrammed, the correct charge content will be present within the floating gate.

Pass disturb is similar to the read disturbs and affects cells belonging to the same string of a cell to be programmed.

The Program disturbs, on the contrary, affect cells that are not to be programmed (inhibit) and belong to the same wordline of those that are to be programmed. In that case the program disturb is strongly related to the voltages and pulse sequences used for the self-boosting techniques. Although the program inhibit boosts the channel potential, soft programming can not be avoided especially when a high number of program pulses are applied.

The criticality of an effective program operation limiting program disturbs and/or possible successive errors is attested by the fact that in NAND memories the program operation should follow a precise and well defined “hierarchy”: it is necessary to start from the cell nearest to the source selector and proceed along the string up to the cell nearest to the drain selector. This procedure is important, because the threshold voltage of a cell depends on the state of the cells placed between the considered cell and the source contact (the background pattern dependency phenomenon); the series resistance of the cells is different if they are programmed or erased.

(further) When manufacturing process scales down to a smaller technology node (i.e., the size of each flash memory cell), the amount of charge that can be trapped within the floating gate also decreases, which exacerbates reliability issues.

**Multi-bit per cell storage (mutil-level):**

The flash memory cell can encode one or more bits of digital data, which is represented by the level of charge stored inside the transistor’s floating gate. Earlier NAND flash chips stored a single bit of data in each cell (i.e., a single floating-gate transistor), which was referred to as single-level cell (SLC) NAND flash. Multi-level cell (MLC) NAND flash stores 2-bit value (00, 01, 10, and 11). Triple-level cell (TLC) flash stores 3-bit value. Quadruple-level cell (QLC) flash stores 4-bit value. The benefits of multi-bit per cell storage is the additional capacity of the SSD without increasing the chip size, while it also decreases reliability by making the cells more difficult to correctly store and read the bits.

**NAND Flash Memory Organization:**

The flash memory is spread across multiple flash chips (typical values: 4, 16 chips), where each chip contains one or more flash *dies*, which are individual pieces of silicon wafer that are connected together to the pins of the chip. Each chip is connected to one or more physical memory channels, and these memory channels are not shared across chips. A flash die operates independently of other flash dies, and contains between one and four *planes*. Each plane contains hundreds to thousands of flash *blocks*. Each block is a 2D array that contains hundreds of rows of flash cells (typically 256-1024 rows) where the rows store contiguous pieces of data.

The planes can execute flash operations in parallel, but the planes within a die share a single set of data and control buses. Hence, an operation can be started in a different plane in the same die in a pipelined manner, every cycle.

Data in a block is written at the unit of a *page*, which is typically between 8 and 16 KiB in size in NAND flash memory. All read and write operations are performed at the granularity of a page. Each block typically contains hundreds of pages.

The controller firmware groups blocks with the same ID number across multiple chips and planes together into a *superblock*. Within each superblock, the pages with the same page number are considered a *superpage*. The controller opens one superblock (i.e., an empty superblock is selected for write operations) at a time, and typically writes data to the NAND flash memory one superpage at a time to improve sequential read/write performance and make error correction efficient, since some parity information is kept at superpage granularity. Having the ability to write to all of the pages in a superpage simultaneously, the SSD can fully exploit the internal parallelism offered by multiple planes/chips, which in turn maximizes write throughput.

**NAND Integrated Circuit:**

Charge pumps are used to generate all the needed voltages within the chip

In multilevel storage, cell’s gate biasing voltages need to be very accurate and voltage regulators become a must.

The Row Decoder is the block in charge of addressing and biasing each single wordline and it is located between the planes. Bitlines are connected to a sensing circuit. The purpose of sense amplifiers is to read the analog information stored in the memory cell.

The Row Decoder, also called Wordline Decoder or Wordline Driver.

Especially, SSDs call for a higher read and write throughputs; in other words, SSDs need to manage more NAND dies in parallel. Basically, there are a couple of options:

* The first one is to increase the number of dies per channel;
* The second option is to increase the number of channels.

Flash chip controllers (FCCs): A Flash chip controller is assigned to a flash memory channel for data and control connection.

DRAM: The on-board DRAM memory stores various controller metadata (e.g., how host memory addresses map to physical SSD addresses) and to cache relevant (e.g., frequently accessed) SSD pages.

SSD Controller: The SSD controller is responsible for (1) handling I/O requests received from the host, (2) ensuring data integrity and efficient storage, and (3) managing the underlying NAND flash memory.